EC-101 (Fundamentals of Electronics Engineering) B. Tech. 2nd (CBCS)

Time: 3 Hours Max. Marks: 60

The candidates shall limit their answers precisely within the answerbook (40 pages) issued to them and no supplementary/continuation sheet will be issued.

Note: Attempt five Questions in all. Selecting One Question from each section A, B, C and D. Section E is Compulsory.

SECTION - A

- 1. Differentiate semiconductor, conductor and insulators on the basis of band gap. (10)
- 2. (a) Define current conduction in semiconductor. (5)
 - (b) With the help of a circuit diagram explain the working of a half-wave rectifier. (5)

SECTION - B

- Explain the BJT characteristics in CE configuration. Explain the behaviour of the transistor in active, cut-off and saturation mode. (10)
- 4. (a) Explain the construction and operation of enhancement type MOSFET. (5)
 - (b) Compare the features of BJT and FET. (5)

SECTION - C

- 5. Define the following:-
 - (a) RC phase shift oscillator
 - (b) Calpitt oscillator (10)

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6. Draw the circuit of an adder operational amplifier using inverting amplifier configuration. Write an equation for the output voltage of this circuit. (10)

SECTION - D

- 7. What are universal gates? Implement all basics gates using universal gates. (10)
- 8. (a) Describe the operation of CRO with neat block diagram. (5)
 - (b). Discuss the importance of 1's and 2's compliment numbers. (5)

SECTION - E (Compulsory)

- 9. (i) What are the charge carriers in n- type and p-type semiconductor?
 - (ii) Define term photodiode.
 - (iii) What is ripple factor?
 - (iv) Explain why BJT's are called bipolar devices and FET's are called unipolar devices?
 - (v) How is drain current controlled in a JFET.
 - (vi) What is an oscillator? How does it differ from an amplifier?
 - (vii) Define unit gain amplifier.
 - (viii) Convert the hexadecimal number into decimals A13B.
 - (ix) What is the purpose of triggering circuit in CRO?
 - (x) Define XNOR gate. (10×2=20)